

NP60N04MUK, NP60N04NUK

MOS FIELD EFFECT TRANSISTOR

R07DS0597EJ0100 Rev.1.00 Jan 11, 2012

Description

These products are N-channel MOS Field Effect Transistors designed for high current switching applications.

Features

• Super low on-state resistance

 $R_{DS(on)} = 4.3 \text{ m}\Omega \text{ MAX.} (V_{GS} = 10 \text{ V}, I_D = 30 \text{ A})$

- Low C_{iss} : $C_{iss} = 2450 \text{ pF TYP.} (V_{DS} = 25 \text{ V})$
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	Lead Plating	Packing	Package
NP60N04MUK-S18-AY *1	Pure Sn (Tin)	Tube 50 p/tube	TO-220 (MP-25K)
NP60N04NUK-S18-AY *1			TO-262 (MP-25SK)

Note: *1 Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	40	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	±60	А
Drain Current (pulse) *1	I _{D(pulse)}	±240	А
Total Power Dissipation (T _C = 25°C)	P _{T1}	105	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.8	W
Channel Temperature	T _{ch}	175	°C
Storage Temperature	T _{stg}	-55 to 175	°C
Repetitive Avalanche Current *2	I _{AR}	28	А
Repetitive Avalanche Energy *2	E _{AR}	78	mJ

Notes: *1 $\,T_{C}$ = 25°C, $P_{W} \leq$ 10 $\mu s,\, Duty\,\, Cycle \leq$ 1%

Thermal Resistance

Channel to Case Thermal Resistance $R_{th(ch-C)}$ 1.43 °C/W Channel to Ambient Thermal Resistance $R_{th(ch-A)}$ 83.3 °C/W

^{*2} R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V

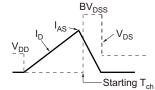
Electrical Characteristics (T_A = 25°C)

Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate to Source Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Forward Transfer Admittance *1	y _{fs}	22	44	_	S	$V_{DS} = 5 \text{ V}, I_{D} = 30 \text{ A}$
Drain to Source On-state Resistance *1	R _{DS(on)}	_	3.6	4.3	mΩ	$V_{GS} = 10 \text{ V}, I_{D} = 30 \text{ A}$
Input Capacitance	C _{iss}	_	2450	3680	pF	V _{DS} = 25 V
Output Capacitance	Coss	_	340	510	pF	$V_{GS} = 0 V$
Reverse Transfer Capacitance	C _{rss}	_	140	260	pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}	_	19	50	ns	$V_{DD} = 20 \text{ V}, I_D = 30 \text{ A}$
Rise Time	t _r	_	9	30	ns	V _{GS} = 10 V
Turn-off Delay Time	t _{d(off)}	_	45	90	ns	$R_G = 0 \Omega$
Fall Time	t _f	_	7	20	ns	
Total Gate Charge	Q_{G}	_	42	63	nC	V _{DD} = 32 V
Gate to Source Charge	Q_{GS}	_	11	_	nC	V _{GS} = 10 V
Gate to Drain Charge	Q_{GD}	_	11	_	nC	$I_D = 60 \text{ A}$
Body Diode Forward Voltage *1	$V_{F(S-D)}$	_	0.9	1.5	V	I _F = 60 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}	_	44	_	ns	I _F = 60 A, V _{GS} = 0 V
Reverse Recovery Charge	Q _{rr}	_	40	_	nC	di/dt = 100 A/μs

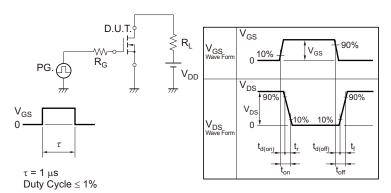
Note: *1 Pulsed test

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $V_{GS} = 20 \rightarrow 0 \text{ V}$



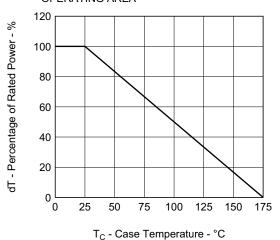
TEST CIRCUIT 2 SWITCHING TIME



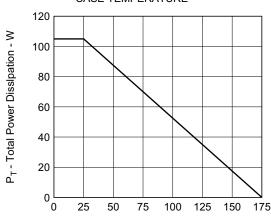
TEST CIRCUIT 3 GATE CHARGE

Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

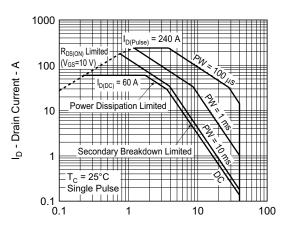


TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



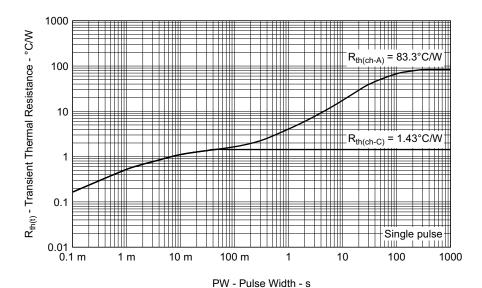
T_C - Case Temperature - °C

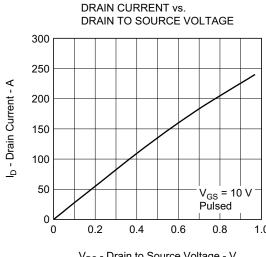
FORWARD BIAS SAFE OPERATING AREA

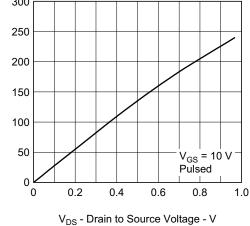


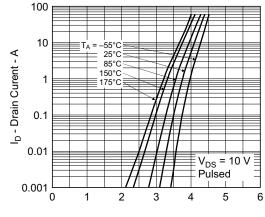
 V_{DS} - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH





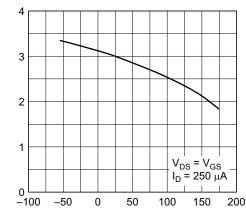




FORWARD TRANSFER CHARACTERISTICS

V_{GS} - Gate to Source Voltage - V

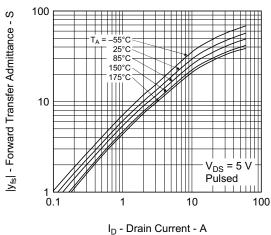




V_{GS(th)} - Gate to Source Threshold Voltage - V

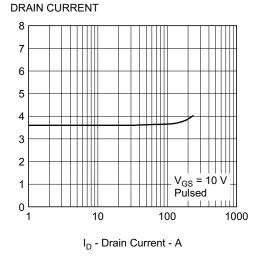
 $R_{DS(on)}$ - Drain to Source On-State Resistance - $m\Omega$



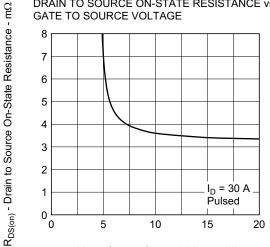


DRAIN TO SOURCE ON-STATE RESISTANCE vs.

T_{ch} - Channel Temperature - °C



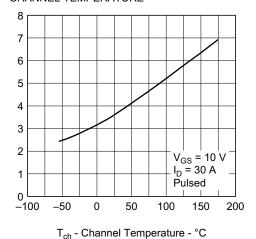
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



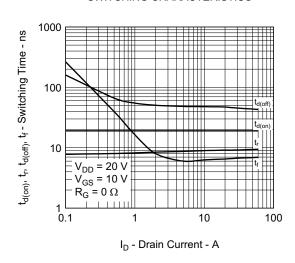
V_{GS} - Gate to Source Voltage - V

 $R_{DS(on)}$ - Drain to Source On-State Resistance - $m\Omega$

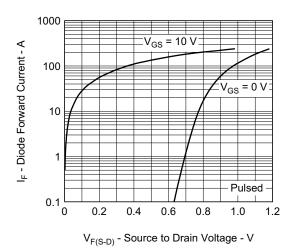
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



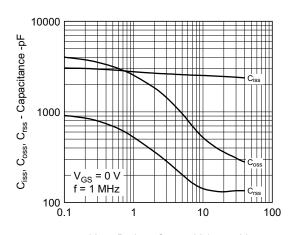
SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

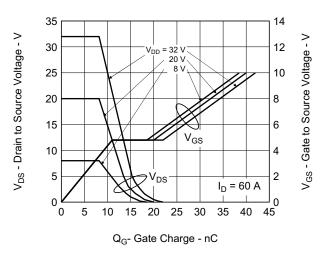


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

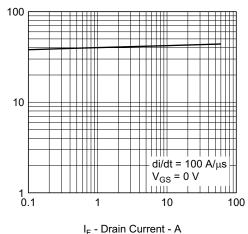


V_{DS} - Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS



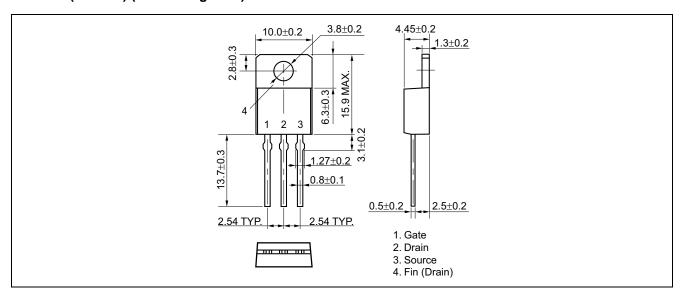
REVERSE RECOVERY TIME vs. **DRAIN CURRENT**



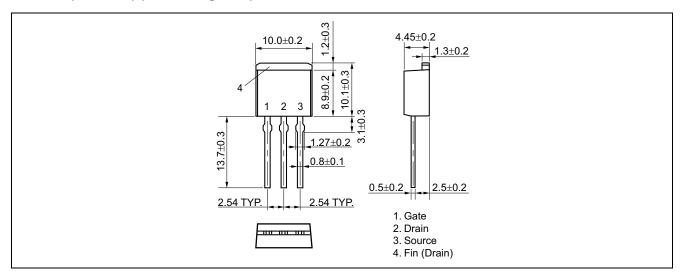
t_{rr} - Reverse Recovery Time - ns

Package Drawing (Unit: mm)

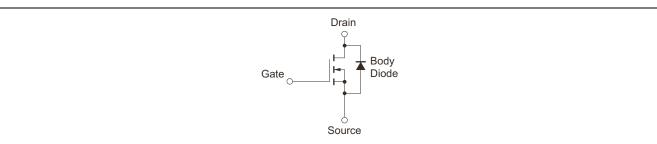
TO-220 (MP-25K) (Mass: 1.9 g TYP.)



TO-262 (MP-25SK) (Mass: 1.8 g TYP.)



Equivalent Circuit



Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Revision History

NP60N04MUK, NP60N04NUK Data Sheet

		Description				
Rev.	Date	Page	Page Summary			
1.00	Jan 11, 2012	_	First Edition Issued			

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